

MPSA63 is PNP silicon darlington transistor designed for preamplifier input applications.

TO-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCES	30V
Collector-Base Voltage	VCBO	30V
Emitter-Base Voltage	VEBO	10V
Collector Current	IC	300mA
Total Power Dissipation	Ptot	625mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BVCES	30		V	IC=100μA VBE=0
Collector-Base Breakdown Voltage	BVCBO	30		V	IC=100μA IE=0
Emitter-Base Breakdown Voltage	BVEBO	10		V	IE=100μA IC=0
Collector Cutoff Current	ICBO		100	nA	VCB=20V IE=0
D.C. Current Gain	HFE	10K			IC=100mA VCE=5V*
		5K			IC=10mA VCE=5V
Collector-Emitter Saturation Voltage	VCE(sat)		1.5	V	IC=100mA IB=0.1mA*
Current Gain-Bandwidth Product	fT	125		MHz	IC=10mA VCE=5V

* Pulse Test : Pulse Width = 300μs, Duty Cycle = 1%.



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